# **RECTRON** SEMICONDUCTOR **TECHNICAL SPECIFICATION**



## SCHOTTKY BARRIER RECTIFIER

VOLTAGE RANGE 100 Volts CURRENT 10 Amperes

### **FEATURES**

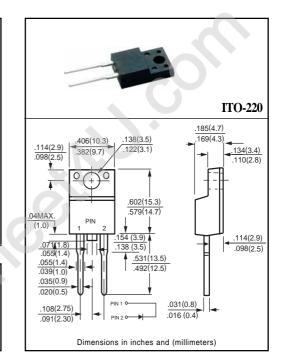
- \* Low switching noise
- \* Low forward voltage drop
- \* Low thermal resistance
- \* High current capability
- \* High switching capability
- \* High surge capabitity
- \* High reliability

### **MECHANICAL DATA**

- \* Case: ITo-220 molded plastic
- \* Epoxy: Device has UL flammability classification 94V-O
- \* Lead: MIL-STD-202E method 208C guaranteed
- \* Mounting position: Any
- \* Weight: 2.24 grams

#### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%.



#### MAXIMUM RATINGS (At TA = 25°C unless otherwise noted)

RATINGS	SYMBOL	ISR10100		
Maximum Recurrent Peak Reverse Voltage	Vrrm	100		
Maximum RMS Voltage	Vrms	70		
Maximum DC Blocking Voltage	VDC	100		
Maximum Average Forward Rectified Current at Derating Case Temperature	ю	10		
Peak Forward Surge Current 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)	IFSM	150	Amps	
Typical Thermal Resistance (Note 1)	RθJC	3	°C/W	
Typical Junction Capacitance (Note 3)	CJ	500	pF	
Operating Temperature Range	TJ	-55 to + 150		
Storage Temperature Range	Tstg	-55 to + 150		

#### ELECTRICAL CHARACTERISTICS (At TA = 25°C unless otherwise noted)

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CHARACTERISTICS		SYMBOL		ISR10100	UNITS
Maximum Instantaneous Forward Voltage at 10.04	DC	VF		.80	Volts
Maximum Average Reverse Current	@Tc = 25°C	la.		190	uAmps
at Rated DC Blocking Voltage	@Tc = 125°C	l R		15	mAmps
NOTES : 1. Thermal Resistance Junction to Case.			2		2005-7

NOTES: 1. Thermal Resistance Junction to Case.

2. Suffix "A" = Common Anode.

3. Measured at 1 MHz and applied reverse voltage of 4.0 volts.

4 "Fully ROHS compliant", "100% Sn plating (Pb-free)".

### RATING AND CHARACTERISTIC CURVES (ISR10100)

